

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Payton

In re Patent Application of) Art Unit: 2812
Shunpei YAMAZAKI et al.) Examiner: S. Isaac
Serial No. 10/072,931)
Filed: February 12, 2002)
For: METHOD OF MANUFACTURING) Date: October 30, 2002
A SEMICONDUCTOR DEVICE)
)

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

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OCT 30 2002
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Sir:

Please preliminarily amend the above-identified application as follows:

IN THE CLAIMS:

Please add new claims 46-77 as follows:

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--46. A method of manufacturing a semiconductor device comprising:
forming a first semiconductor film having an amorphous structure over a
substrate;
providing the first semiconductor film with a material for promoting
crystallization;
heating the first semiconductor film for crystallizing;
irradiating the first semiconductor film with a laser light for improving
crystallinity;
forming a barrier layer over the first semiconductor film having crystalline
structure;
forming a ~~second semiconductor film over the barrier layer~~;
forming a third semiconductor film over the second semiconductor film, the
third semiconductor film comprising an inert gas element;